

2823

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DOCKET NO.: 8733-6386

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

Re: Serial No.: 09/170,625
Applicant(s): Duck-Kyun CHOI
Filing Date: October 13, 1998
For: METHOD FOR FABRICATING A THIN FILM TRANSISTOR
Group Art Unit: 2823
Examiner: S. Hawranek

SIR:

Attached hereto for filing are the following papers:

SUPPLEMENTAL AMENDMENT

Our check in the amount of \$ 0.00 is attached covering any required fees. In the event any variance exists between the amount enclosed and the Patent Office charges for filing the above-noted documents, including any fees required under 37 C.F.R. §1.136 for any necessary Extension of Time to make the filing of the attached documents timely, please charge or credit the difference to our Deposit Account No. 50-0911. Further, if these papers are not considered timely filed, then a petition is hereby made under 37 C.F.R. §1.136 for the necessary extension of time. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

LONG ALDRIDGE & NORMAN LLP

James M. Heintz

Attorney of Record

Registration No.: 41,838

Docket No. 8733-6836



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

10/B
J. Mackey
3-270

IN RE APPLICATION OF: Duck-Kyun CHOI

GAU: 2823

SERIAL NO: 09/170,625

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SIR:

Further to the Amendment filed March 8, 2000, in response to the nonfinal Office Action dated December 8, 1999, Applicant requests that the application be further amended as follows:

IN THE CLAIMS:

Please amend the claims as follows:

2. (Amended) The method of fabricating a thin film transistor according to claim 1, wherein the substrate includes [one of a glass and an oxide layer on a glass] a material selected from the group consisting of a glass and a glass having an oxide layer formed thereon.

3. (Amended) The method of fabricating a thin film transistor according to claim 1, wherein the substrate [is prepared by depositing a silicon wafer or an oxide layer on a silicon wafer] includes a material selected from the group consisting of a silicon wafer and a silicon wafer having an oxide layer formed thereon.